



Fig 1

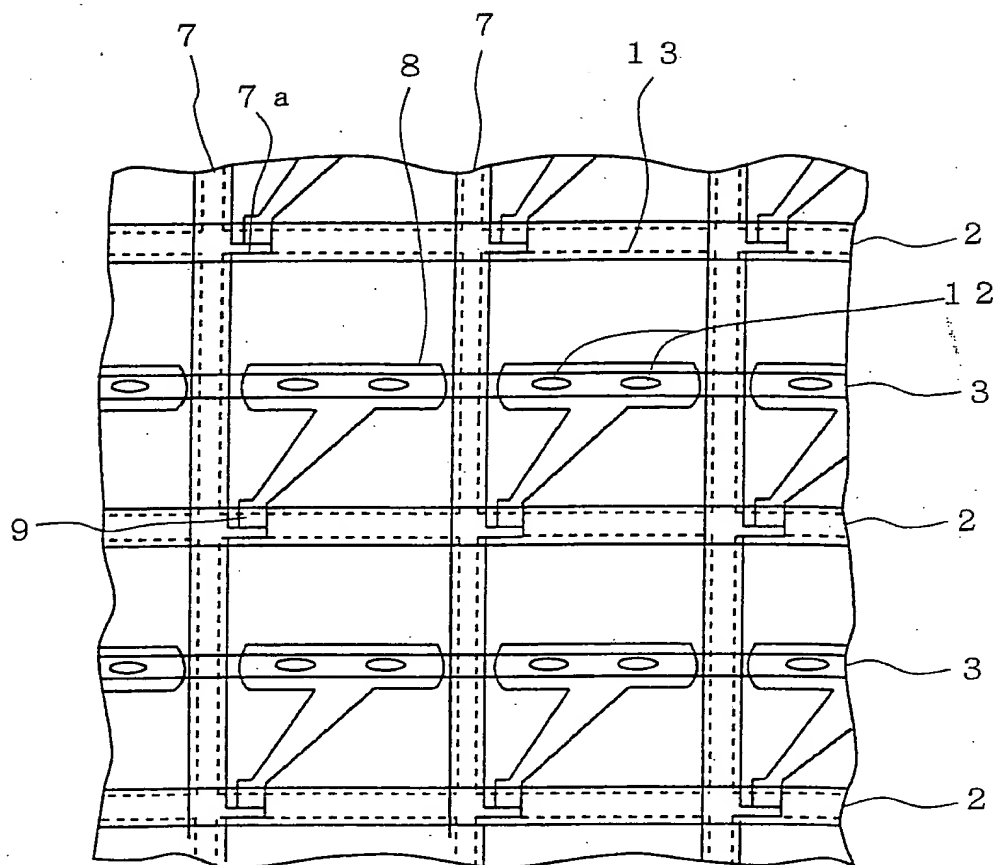


Fig 2

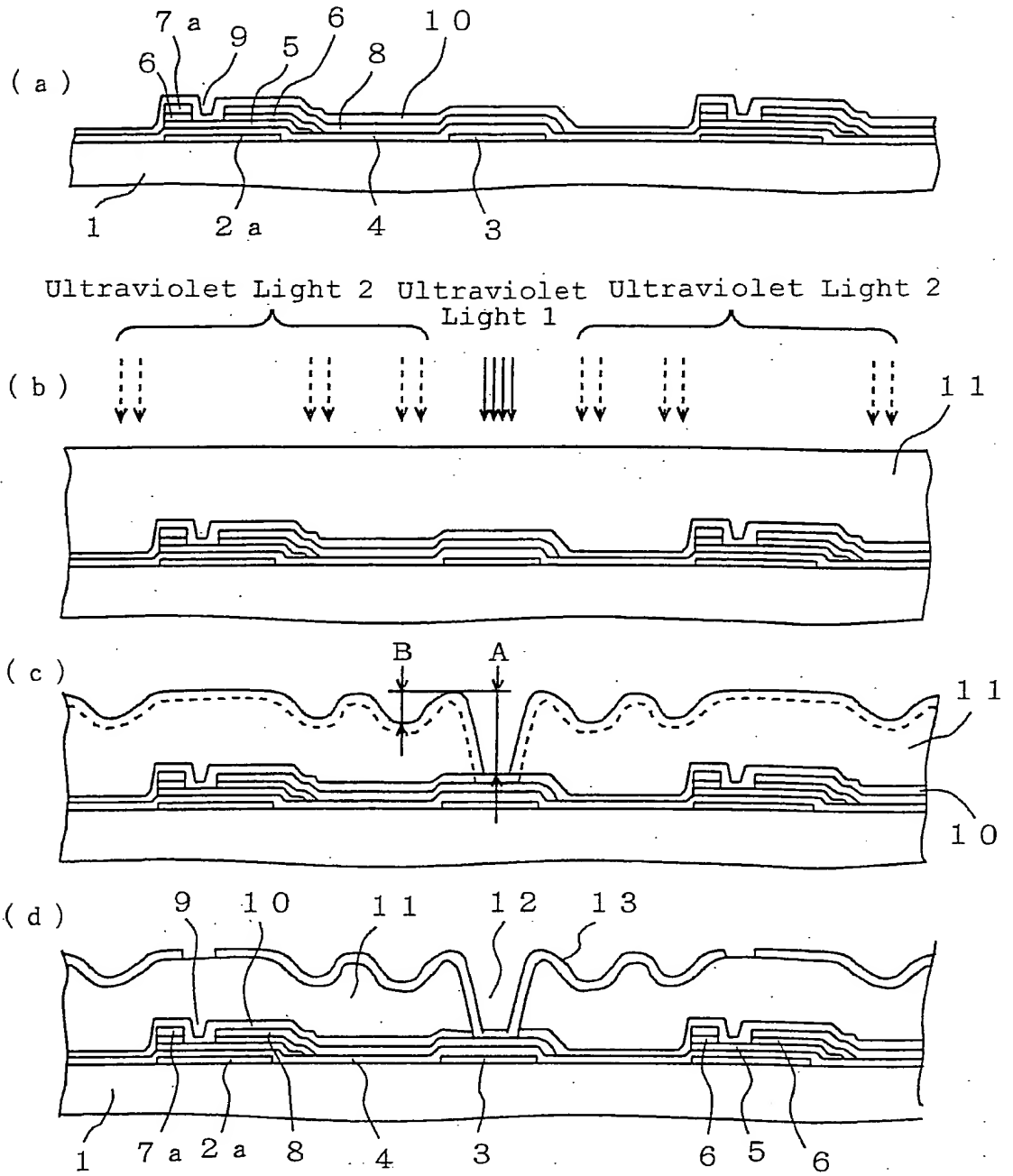
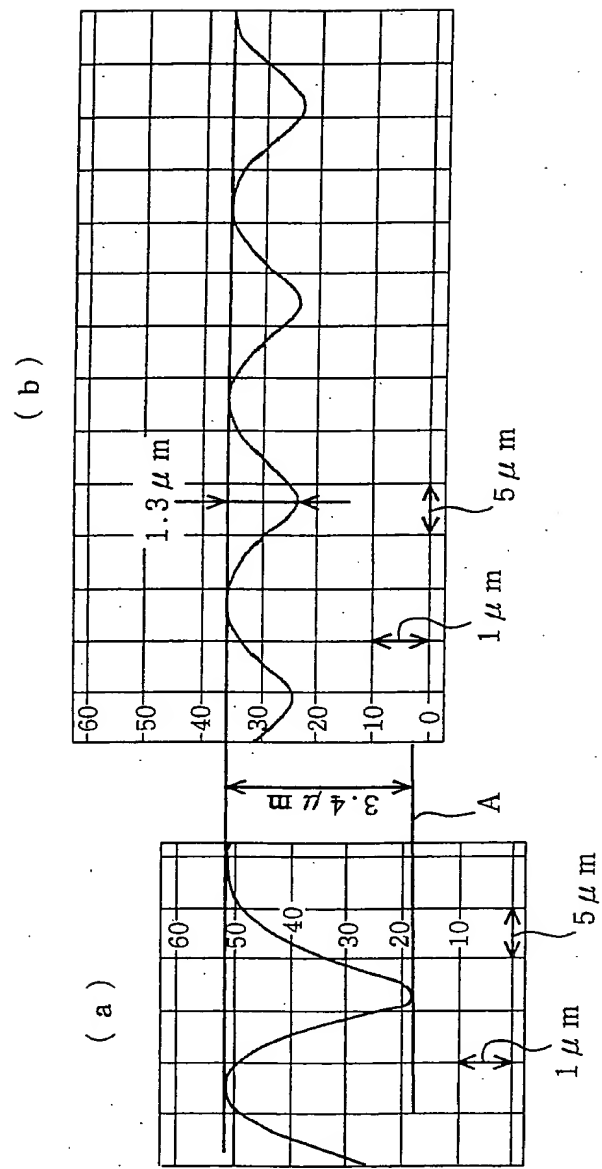


Fig. 3



The figure consists of two cross-sectional diagrams of a semiconductor device. The upper diagram shows a substrate 1 with a thin layer 10 on its surface. Below the substrate, there are several rectangular features 17. Arrows labeled 'a' point downwards towards the substrate, representing incident light. Arrows labeled 'b' point upwards from below the substrate, also representing incident light. The lower diagram shows a similar structure with labels 1, 6, 5, 6, 3, 8, 4, 2a, 7a, and 11. It illustrates the internal layers and components of the device, including what appears to be a waveguide or channel structure.

Fig 5

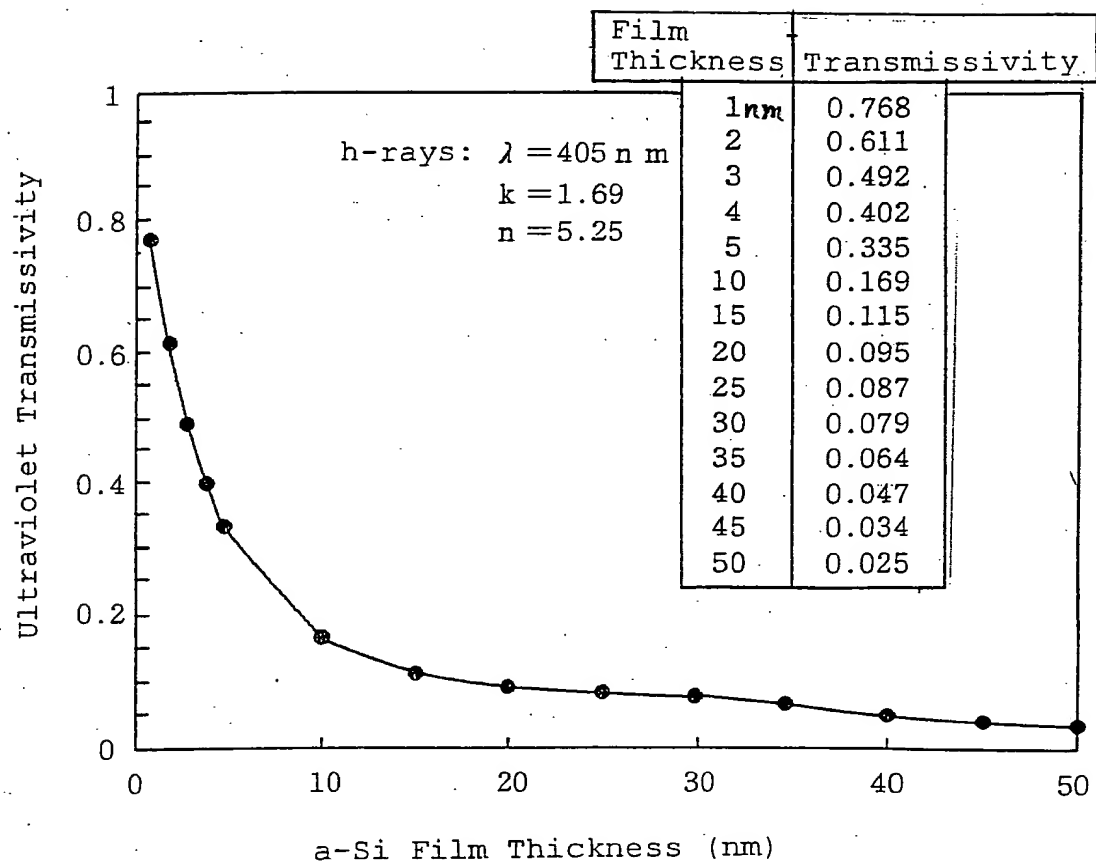


Fig 6

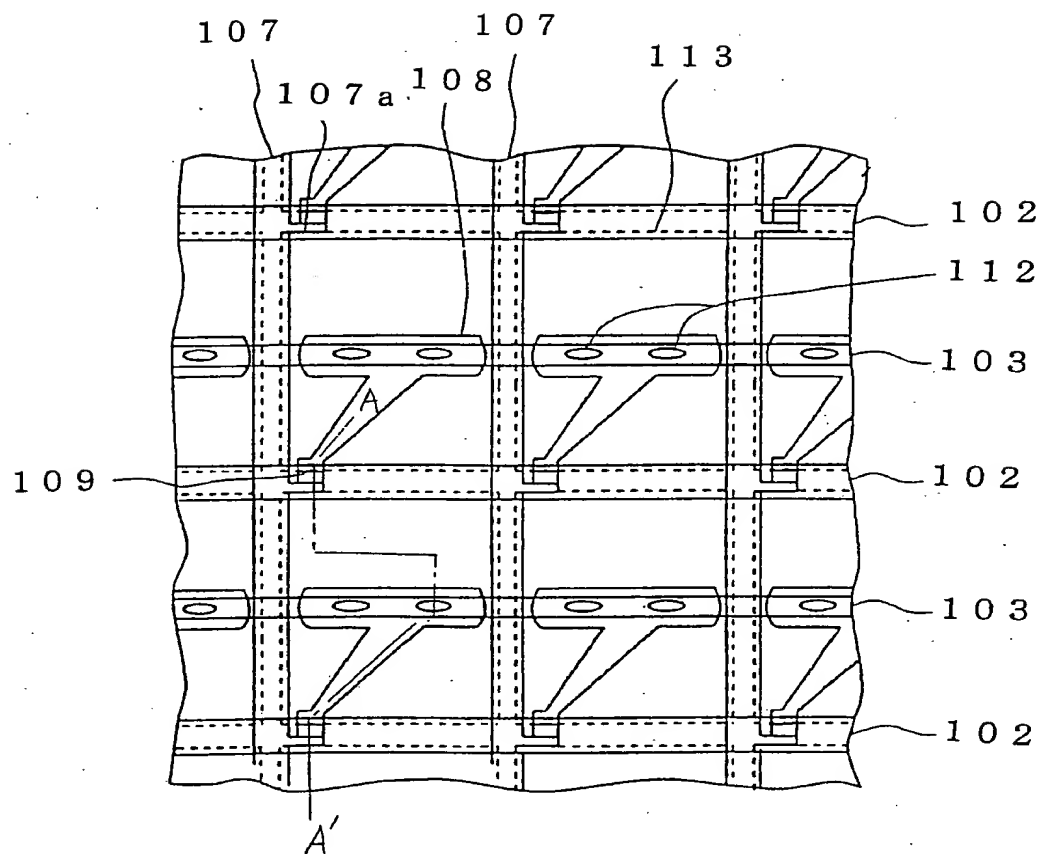


Fig. 7

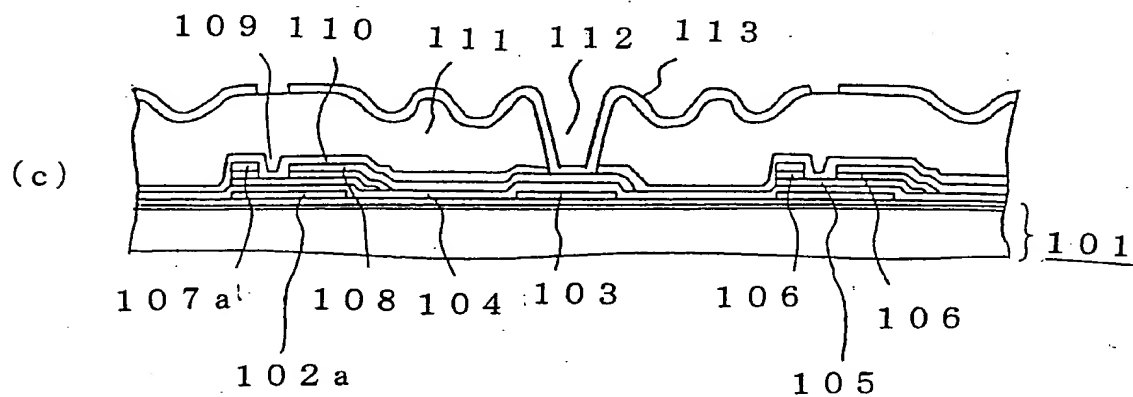
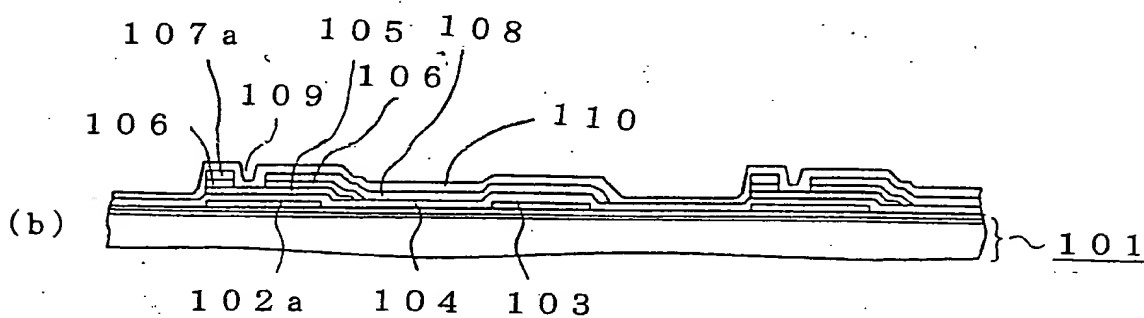
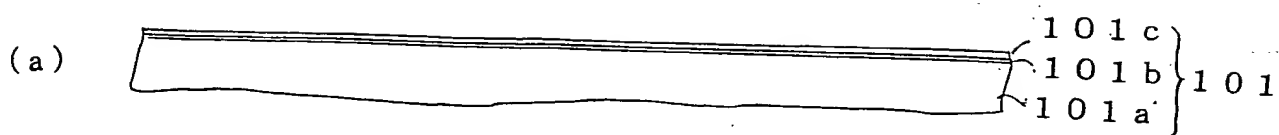
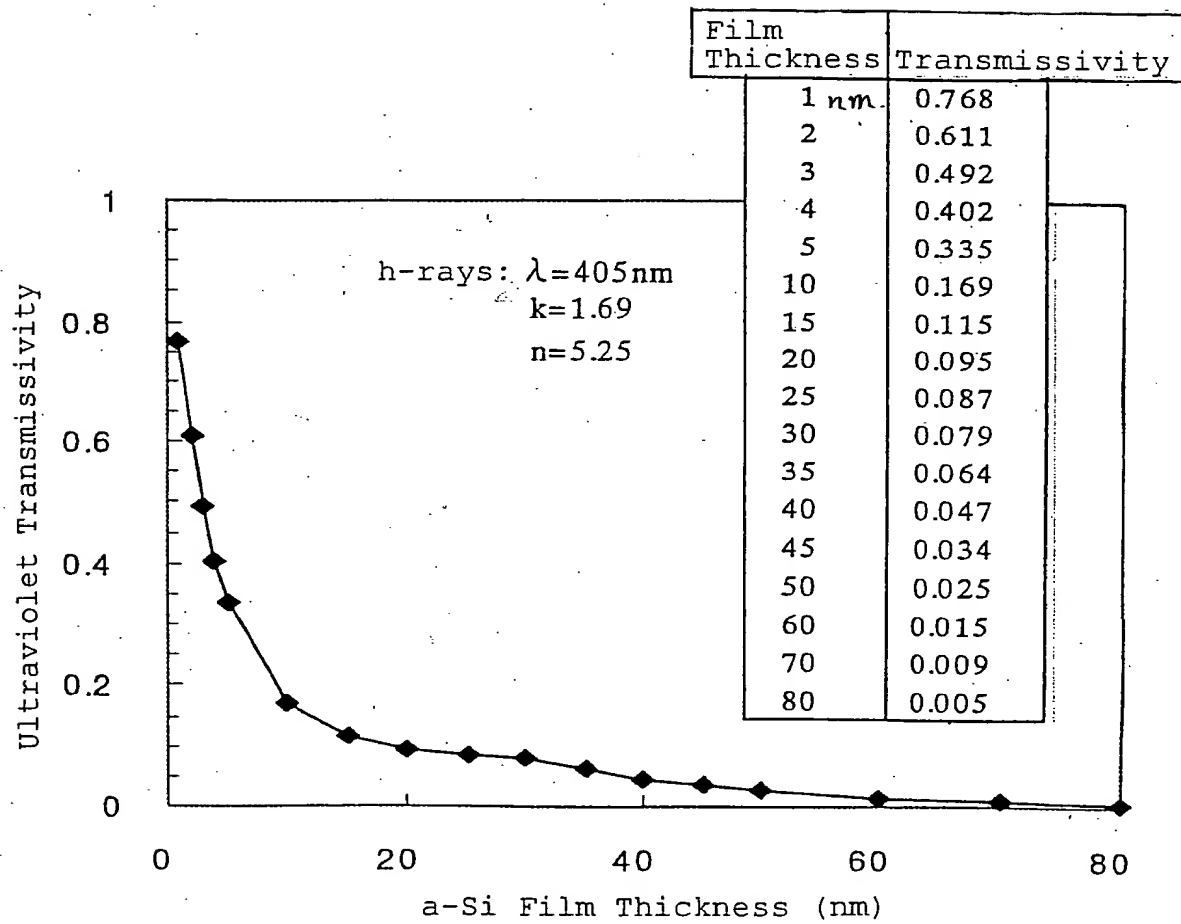


Fig 8



Ultraviolet Transmissivity (Calculated Value) with respect to
a-Si Film Thickness

Fig 9

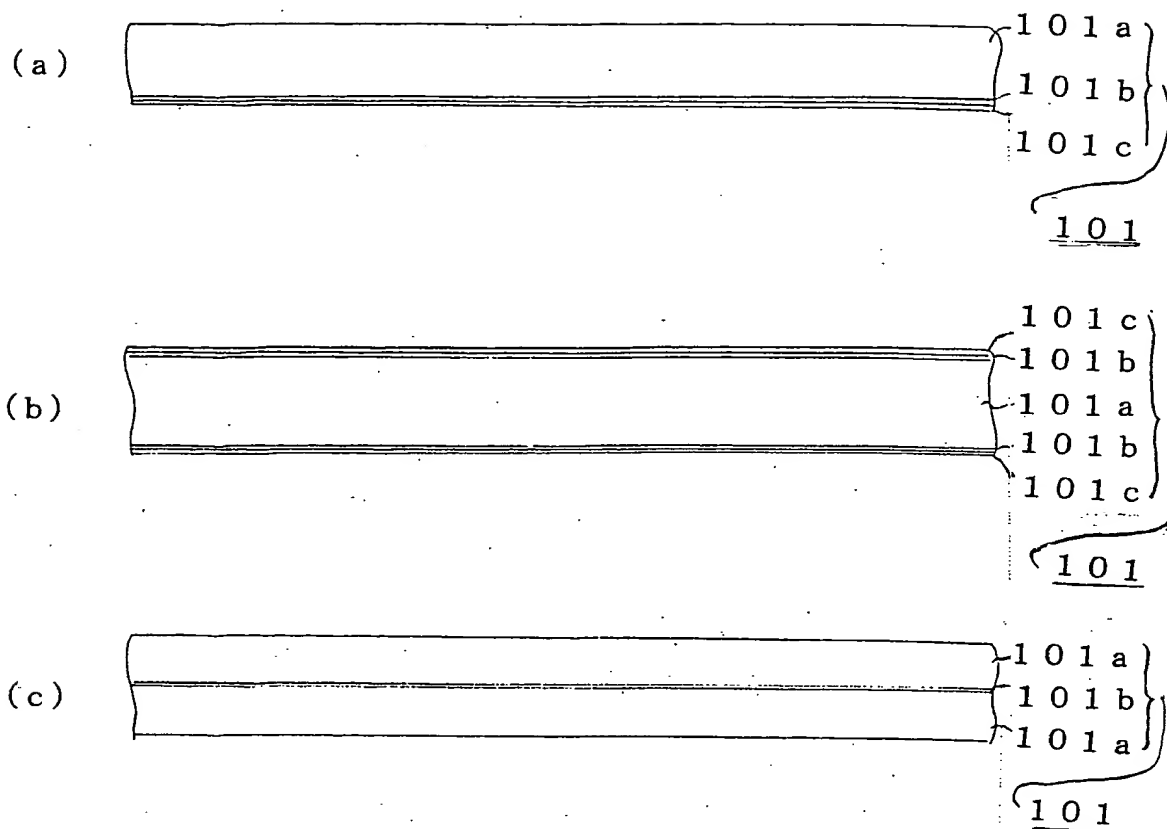


Fig. 10

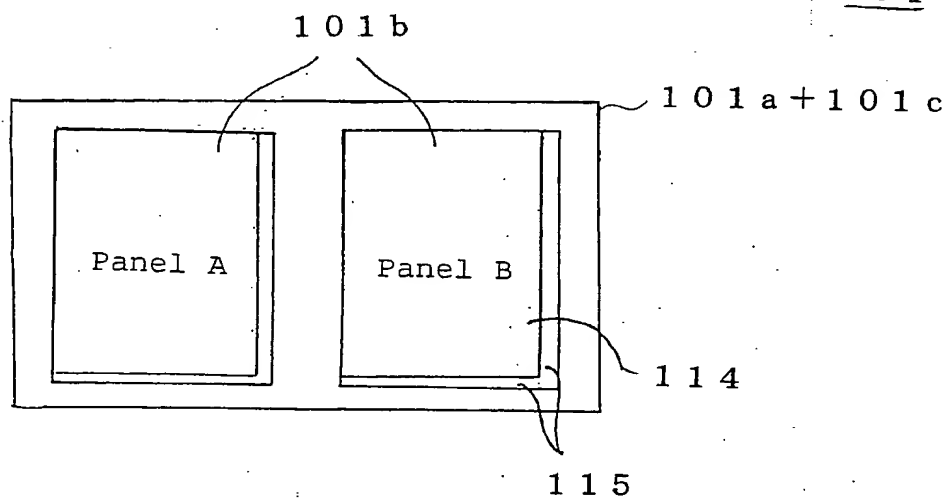
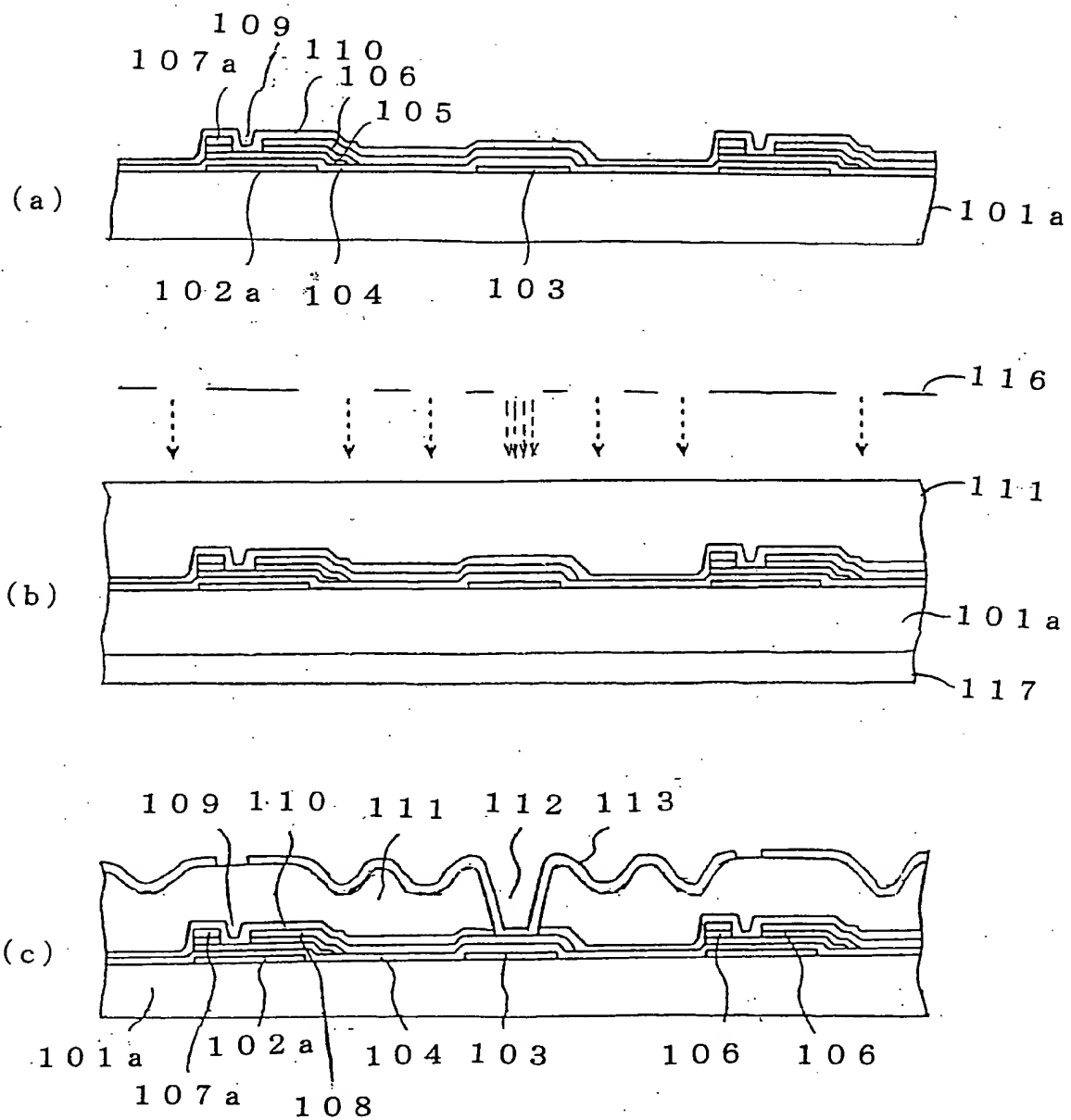


Fig 11



F i g . 1 2

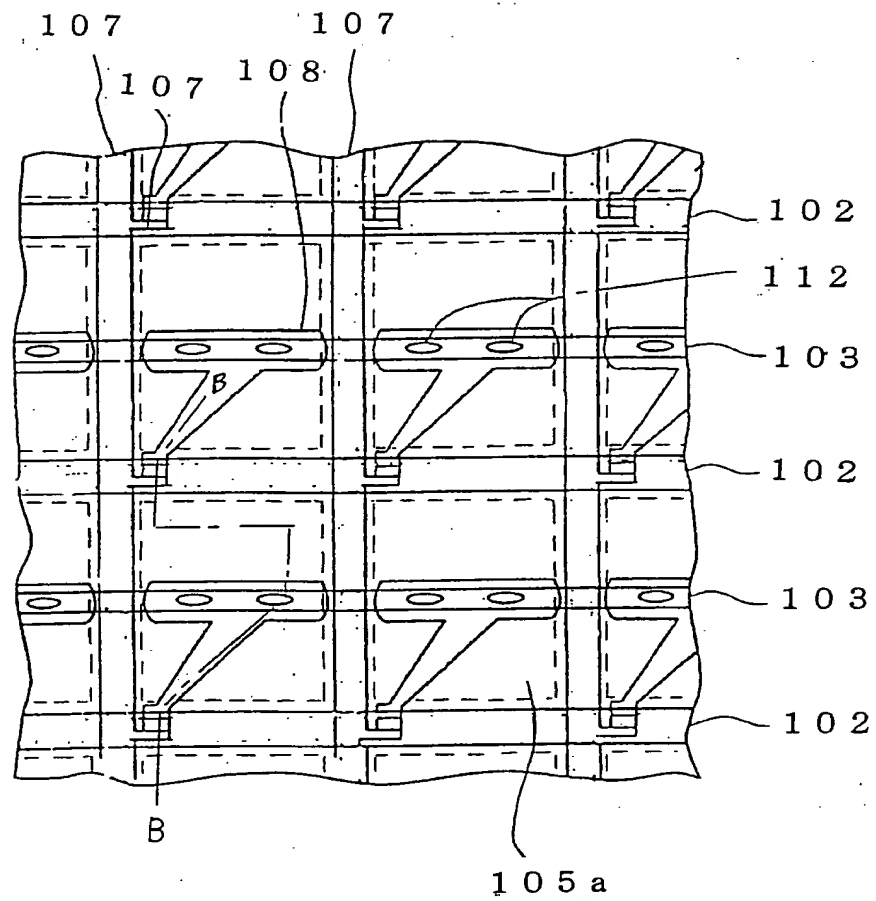


Fig. 13

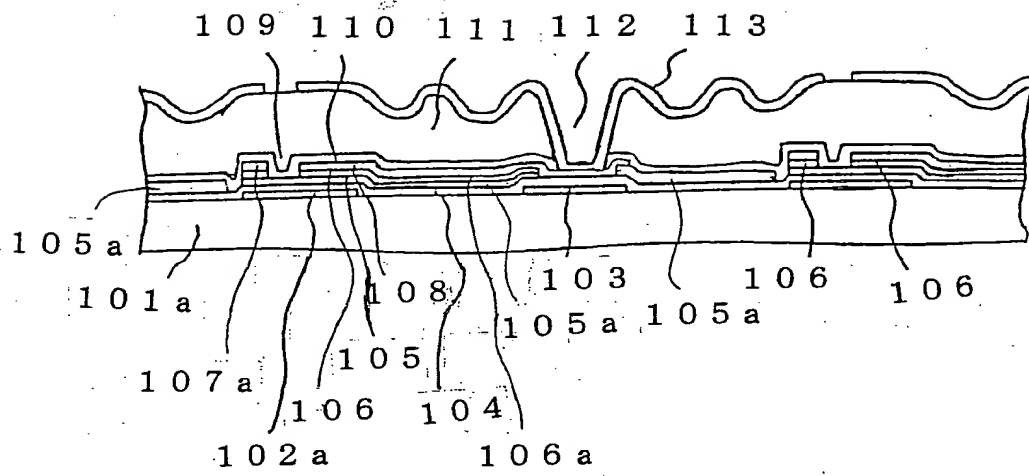


Fig. 14

